

Daniel C Worledge

List of Publications by Year in descending order

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43
papers

2,871
citations

218677

26
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265206

42
g-index

45
all docs

45
docs citations

45
times ranked

3034
citing authors

#	ARTICLE	IF	CITATIONS
1	A new spin on magnetic memories. Nature Nanotechnology, 2015, 10, 187-191.	31.5	645
2	Spin torque switching of 20-nm magnetic tunnel junctions with perpendicular anisotropy. Applied Physics Letters, 2012, 100, .	3.3	256
3	Magnetoresistance measurement of unpatterned magnetic tunnel junction wafers by current-in-plane tunneling. Applied Physics Letters, 2003, 83, 84-86.	3.3	206
4	Anneal-tunable Curie temperature and transport of La _{0.67} Ca _{0.33} MnO ₃ . Journal of Applied Physics, 1996, 80, 5158-5161.	2.5	160
5	Dependence of Voltage and Size on Write Error Rates in Spin-Transfer Torque Magnetic Random-Access Memory. IEEE Magnetics Letters, 2016, 7, 1-4.	1.1	119
6	A Study of Write Margin of Spin Torque Transfer Magnetic Random Access Memory Technology. IEEE Transactions on Magnetics, 2010, 46, 2322-2327.	2.1	115
7	Spin flop switching for magnetic random access memory. Applied Physics Letters, 2004, 84, 4559-4561.	3.3	114
8	Negative Spin-Polarization of SrRuO ₃ . Physical Review Letters, 2000, 85, 5182-5185.	7.8	113
9	Magnetoresistive double spin filter tunnel junction. Journal of Applied Physics, 2000, 88, 5277-5279.	2.5	94
10	Impact of Ta Diffusion on the Perpendicular Magnetic Anisotropy of Ta/CoFeB/MgO. IEEE Magnetics Letters, 2013, 4, 1000104-1000104.	1.1	90
11	On-site Coulomb repulsion in the small polaron system La _{1-x} Ca _x MnO ₃ . Physical Review B, 1998, 57, 15267-15271.	3.2	88
12	Demonstration of ultralow bit error rates for spin-torque magnetic random-access memory with perpendicular magnetic anisotropy. IEEE Magnetics Letters, 2011, 2, 3000204-3000204.	1.1	82
13	Magnetic phase diagram of two identical coupled nanomagnets. Applied Physics Letters, 2004, 84, 2847-2849.	3.3	80
14	Spin-polarized tunneling in La _{0.67} Sr _{0.33} MnO ₃ . Applied Physics Letters, 2000, 76, 900-902.	3.3	65
15	Perpendicular Magnetic Anisotropy and Easy Cone State in Ta/Co ₆₀ Fe ₂₀ B ₂₀ /MgO. IEEE Magnetics Letters, 2015, 6, 1-4.	1.1	55
16	Materials for spin-transfer-torque magnetoresistive random-access memory. MRS Bulletin, 2018, 43, 352-357.	3.5	49
17	Maki analysis of spin-polarized tunneling in an oxide ferromagnet. Physical Review B, 2000, 62, 447-451.	3.2	47
18	Electric field-induced ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction under dc bias voltages. Applied Physics Letters, 2014, 105, .	3.3	44

#	ARTICLE	IF	CITATIONS
19	Development of perpendicularly magnetized Ta CoFeB MgO-based tunnel junctions at IBM (invited). Journal of Applied Physics, 2014, 115, .	2.5	37
20	Transport across conducting ferromagnetic oxide/metal interfaces. Applied Physics Letters, 1998, 73, 1736-1738.	3.3	36
21	Conducting atomic-force-microscope electrical characterization of submicron magnetic tunnel junctions. Applied Physics Letters, 2003, 82, 4522-4524.	3.3	34
22	Theory of Spin Torque Switching Current for the Double Magnetic Tunnel Junction. IEEE Magnetics Letters, 2017, 8, 1-5.	1.1	34
23	Two-level BEOL processing for rapid iteration in MRAM development. IBM Journal of Research and Development, 2006, 50, 41-54.	3.1	31
24	Single-domain model for toggle MRAM. IBM Journal of Research and Development, 2006, 50, 69-79.	3.1	30
25	Thermally activated switching in spin-flop tunnel junctions. Applied Physics Letters, 2005, 86, 252506.	3.3	28
26	Effect of annealing temperature on local distortion of La _{0.67} Ca _{0.33} MnO ₃ thin films. Physical Review B, 2000, 61, 11373-11378.	3.2	26
27	Optimization of Tunneling Magnetoresistance in Perpendicular Magnetic Tunnel Junctions With Co Pd Reference Layers. IEEE Magnetics Letters, 2013, 4, 3000104-3000104.	1.1	23
28	Rapid-turnaround characterization methods for MRAM development. IBM Journal of Research and Development, 2006, 50, 55-67.	3.1	22
29	Dynamo waves in semi-infinite and finite domains. Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences, 1997, 453, 119-143.	2.1	21
30	Growth and small polaron properties of epitaxial La _{1-x} Ca _x MnO ₃ thin films. Journal of Applied Physics, 1998, 83, 5913-5916.	2.5	20
31	Reduction of positional errors in a four-point probe resistance measurement. Applied Physics Letters, 2004, 84, 1695-1697.	3.3	19
32	Theory for symmetric toggle magnetic random access memory. Applied Physics Letters, 2007, 90, 222506.	3.3	14
33	Reliable Five-Nanosecond Writing of Spin-Transfer Torque Magnetic Random-Access Memory. IEEE Magnetics Letters, 2019, 10, 1-4.	1.1	14
34	Low power scaling using parallel coupling for toggle magnetic random access memory. Applied Physics Letters, 2006, 88, 262505.	3.3	10
35	Materials investigation for thermally-assisted magnetic random access memory robust against 400°C temperatures. Journal of Applied Physics, 2015, 117, .	2.5	9
36	Micromagnetics of Spin-Flop Bilayers: S, C, and Vortex Spin States. IEEE Transactions on Magnetics, 2010, 46, 2124-2127.	2.1	8

#	ARTICLE	IF	CITATIONS
37	Spin-Transfer-Torque MRAM: the Next Revolution in Memory. , 2022, , .		8
38	Theory for toggle magnetic random access memory: The asymmetric case. Applied Physics Letters, 2007, 91, 162509.	3.3	5
39	Resonant Switching of Two Dipole-Coupled Nanomagnets. IEEE Transactions on Magnetics, 2010, 46, 2112-2115.	2.1	5
40	Demonstration of bi-directional microwave-assisted magnetic reversal in synthetic ferrimagnets. Applied Physics Letters, 2013, 103, .	3.3	4
41	(Invited) Recent Developments in ST-MRAM, Including Scaling. ECS Transactions, 2013, 58, 117-125.	0.5	4
42	Investigations of half and full select disturb rates in a toggle magnetic random access memory. Applied Physics Letters, 2008, 92, 192510.	3.3	3
43	The effect of the annealing temperature on the local distortion of La _{0.67} Ca _{0.33} MnO ₃ thin films. Journal of Synchrotron Radiation, 1999, 6, 682-684.	2.4	0